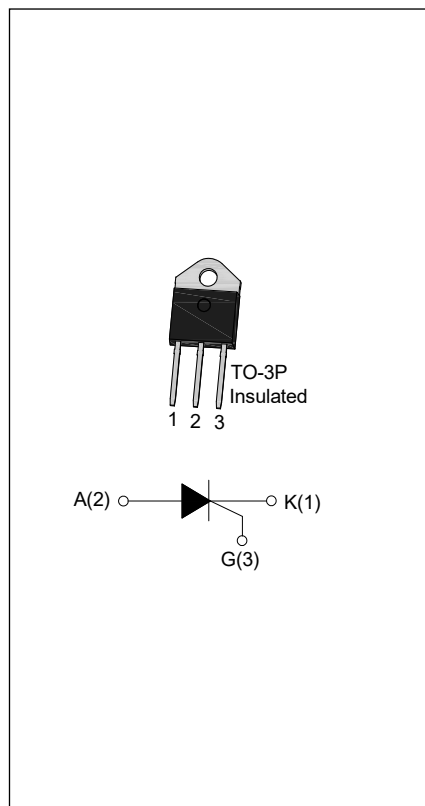




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1275Z SCRs provide high dv/dt rate with high frequency noise immunity. Products are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three pins to external heatsink, JCT1275Z provide an insulation voltage of 2500 V_{RMS}, complying with UL standards (File ref: E252906). Package TO-3P is RoHS compliant. (2011/65/EU)



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	75	A
V_{DRM} / V_{RRM}	1200	V
I_{GT}	10~80	mA

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	°C
Operating junction temperature range		T_j	-40-125	°C
Repetitive peak off-state voltage($T_j=25^\circ\text{C}$)		V_{DRM}	1200	V
Repetitive peak reverse voltage($T_j=25^\circ\text{C}$)		V_{RRM}	1200	V
Non repetitive surge peak Off-state voltage		V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage		V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current	TO-3P(Ins) ($T_c=60^\circ\text{C}$)	$I_{T(RMS)}$	75	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}$)		I_{TSM}	800	A
I^2t value for fusing ($t_p=10\text{ms}$)		I^2t	3200	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)		di/dt	150	$\text{A}/\mu\text{s}$

Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	10	-	80	mA
V_{GT}		-	-	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C } R_L=3.3\text{K}\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	150	mA
I_H	$I_T=1\text{A}$	-	-	120	mA
dv/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$	700	-	-	V/ μs

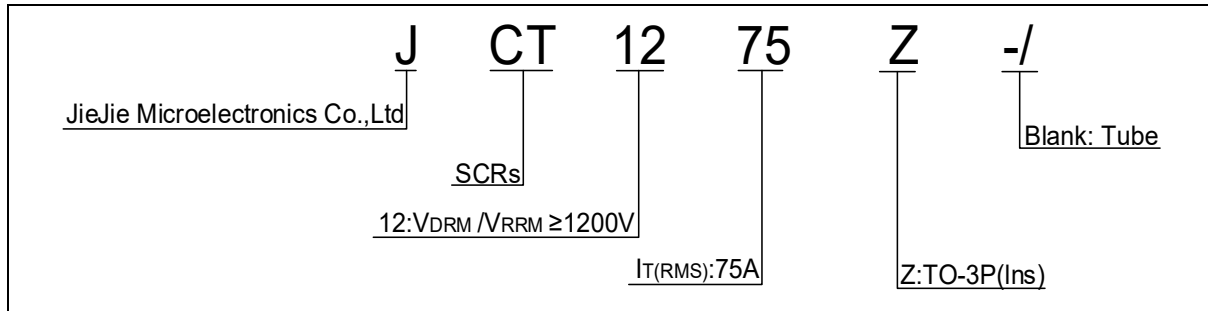
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=100\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	50	μA
I_{RRM}		$T_j=125^\circ\text{C}$	10	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-3P(Ins)	0.60	$^\circ\text{C}/\text{W}$

ORDERING INFORMATION



MARKING

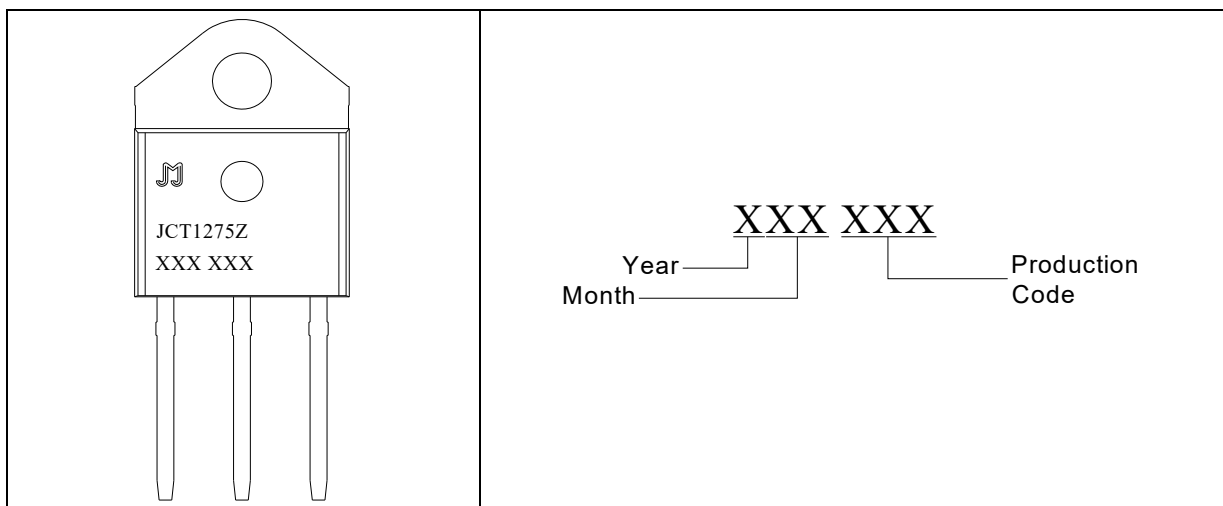


FIG.1: Maximum power dissipation versus RMS on-state current

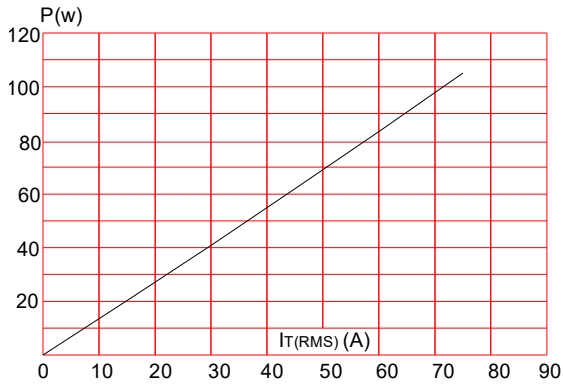


FIG.2: RMS on-state current versus case temperature

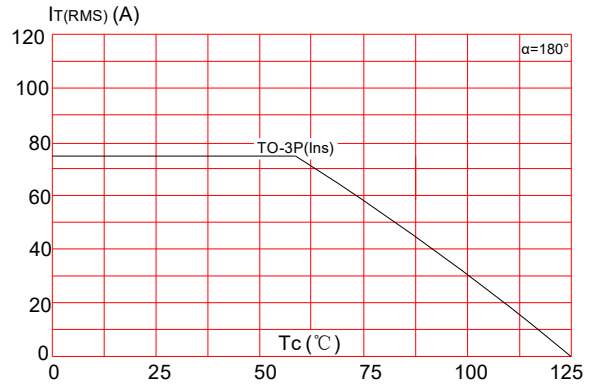


FIG.3: Surge peak on-state current versus number of cycles

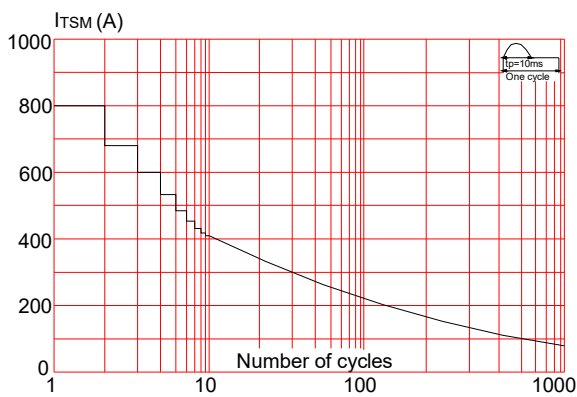


FIG.4: On-state characteristics (maximum values)

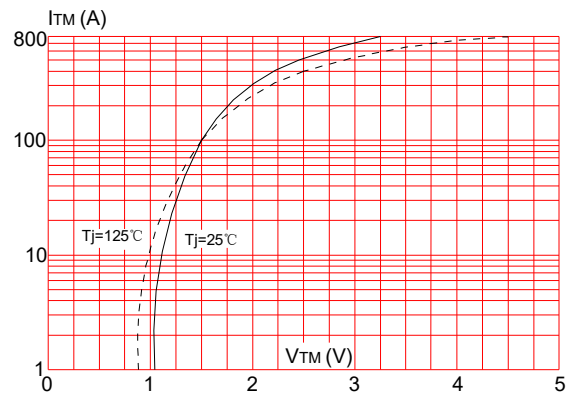


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of $I^2 t$ ($di/dt < 150\text{A}/\mu\text{s}$)

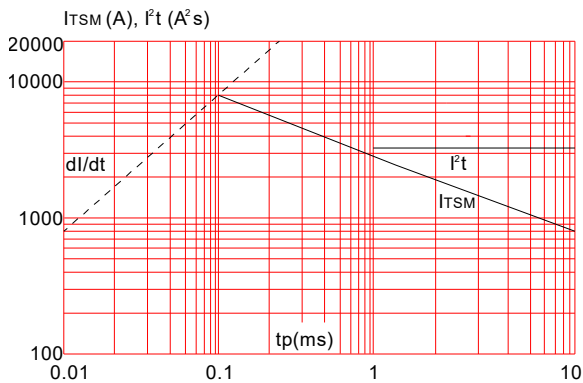
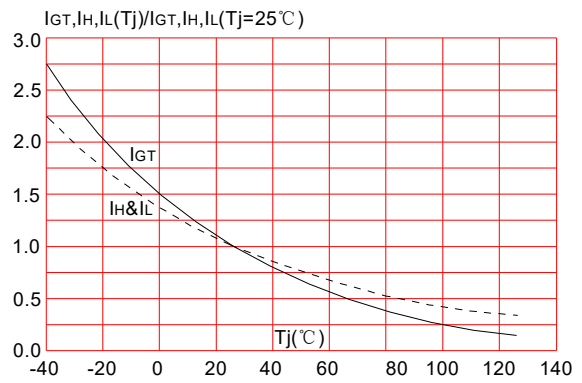


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



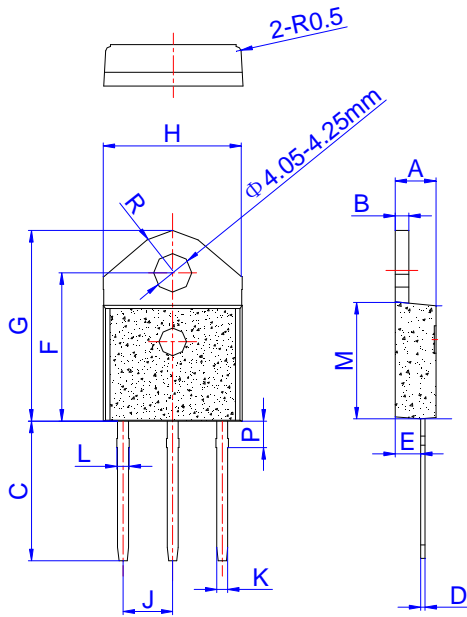
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RPM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT1275Z	1200	10~80	TO-3P	30	Tube

Document Revision History

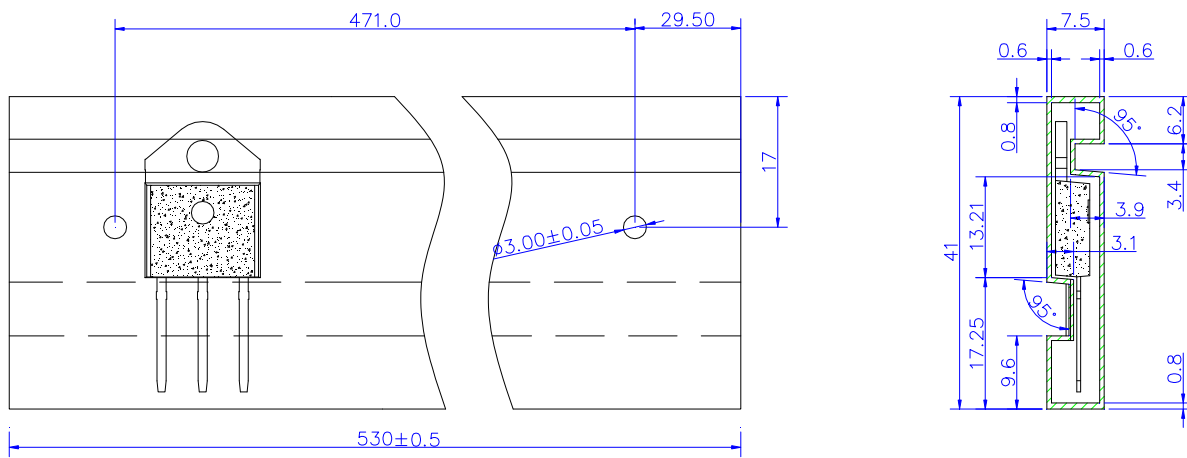
Date	Revision	Changes
Mar 23, 2022	1	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.25		1.45	0.049		0.057
M	12.37		12.77	0.487		0.503
P	2.80		3.00	0.110		0.118
R		4.35			0.171	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-3P	TUBE	30	450	2,250



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